

Appl. No. 09/818,193
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Reply to Office Action of June 14, 2004

Amendments to the Abstract

Please replace the abstract from page 16, lines 2-11 with the following replacement abstract:

~~In one aspect the present invention provides a method~~ A method for manufacturing a silicon carbide semiconductor device. In one embodiment, the method includes the following steps: A layer a layer of silicon dioxide is formed on a silicon carbide substrate to create a silicon dioxide/silicon carbide interface and then nitrogen is incorporated at the silicon dioxide/silicon carbide interface for reduction in an interface trap density. The silicon carbide substrate, in one embodiment, includes a n-type 4H-silicon carbide. In one embodiment, nitrogen is incorporated by annealing the semiconductor device in nitric oxide or nitrous oxide. In another embodiment, nitrogen is incorporated by annealing the semiconductor device in ammonia.

~~In another aspect, the present invention provides a silicon carbide semiconductor device that has a 4H-silicon carbide substrate, a layer of silicon dioxide disposed on the 4H-silicon carbide substrate and a region of substantial nitrogen concentration at the silicon dioxide/silicon carbide interface.~~